MC54/74HCT540

Octal 3-State Inverting Buffer/Line Driver/Line Receiver with LSTTL-Compatible Inputs

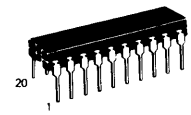
High-Performance Silicon-Gate CMOS

The MC54/74HCT540 is identical in pinout to the LS540. This device may be used as a level converter for interfacing TTL or NMOS to High-Speed CMOS inputs.

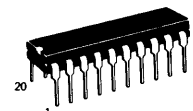
The HCT540 is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HCT540 is similar in function to the HCT541, which has noninverting outputs.

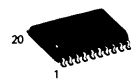
- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 164 FETs or 41 Equivalent Gates



J SUFFIX
CERAMIC
CASE 732-03



N SUFFIX
PLASTIC
CASE 738-03



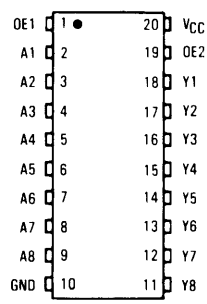
DW SUFFIX
SOIC
CASE 751D-03

ORDERING INFORMATION

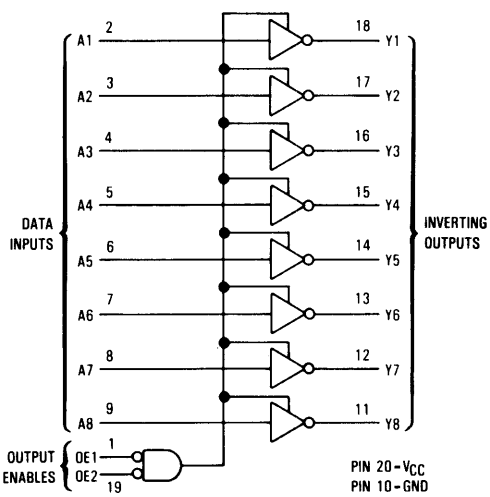
MC74HCTXXXN	Plastic
MC54HCTXXXJ	Ceramic
MC74HCTXXXDW	SOIC

T_A = −55° to 125°C for all packages.
Dimensions in Chapter 6.

PIN ASSIGNMENTS



LOGIC DIAGRAM



FUNCTION TABLE

Inputs			Output
OE1	OE2	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

Z = high impedance
X = don't care

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	−0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	−1.5 to V_{CC} +1.5	V
V_{out}	DC Output Voltage (Referenced to GND)	−0.5 to V_{CC} +0.5	V
I_{in}	DC Input Current, per Pin	±20	mA
I_{out}	DC Output Current, per Pin	±35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±75	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T_{stg}	Storage Temperature	−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: −10 mW/°C from 65° to 125°C
Ceramic DIP: −10 mW/°C from 100° to 125°C
SOIC Package: −7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \le (V_{in} \text{ or } V_{out}) \le V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	−55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25°C to −55°C	≤85°C	≤125°C	
V_{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1 V or V_{CC} − 0.1 V $\|I_{out}\| \le 20$ μA	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} − 0.1 V $\|I_{out}\| \le 20$ μA	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $\|I_{out}\| \le 20$ μA	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH}$ or V_{IL} $\|I_{out}\| \le 6.0$ mA	4.5	3.98	3.84	3.70	
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $\|I_{out}\| \le 20$ μA	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL} $\|I_{out}\| \le 6.0$ mA	4.5	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	5.5	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	5.5	±0.5	±5.0	±10.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0$ μA	5.5	8	80	160	μA

				≥ −55°C	25°C to 125°C	
ΔI_{CC}	Additional Quiescent Supply Current	V_{in} = 2.4 V, Any One Input $V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0$ μA	5.5	2.9	2.4	mA

NOTES:
1. Information on typical parametric values can be found in Chapter 4.
2. Total Supply Current = $I_{CC} + \Sigma\Delta I_{CC}$.

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AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 V ± 10%, C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	Guaranteed Limit			Unit
		25°C to −55°C	≤85°C	≤125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	30	38	45	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	35	44	53	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	45	56	68	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	12	15	18	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	15	15	15	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

C_{PD}	Power Dissipation Capacitance (Per Buffer) Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C, V_{CC} = 5.0 V 50	pF

SWITCHING WAVEFORMS

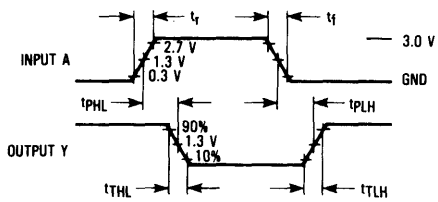


Figure 1.

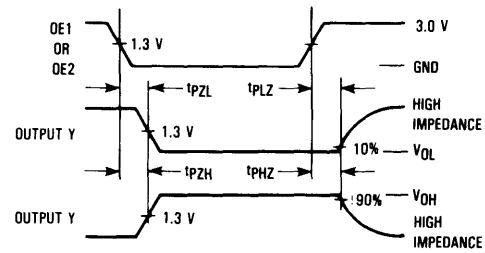
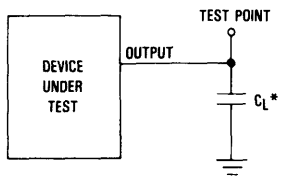


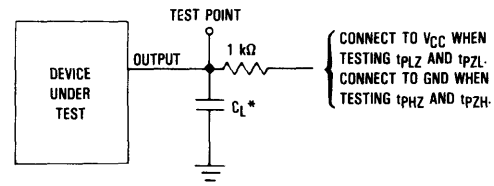
Figure 2.

TEST CIRCUITS



*Includes all probe and jig capacitance.

Figure 3.



*Includes all probe and jig capacitance.

Figure 4.

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9) — Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are enabled.

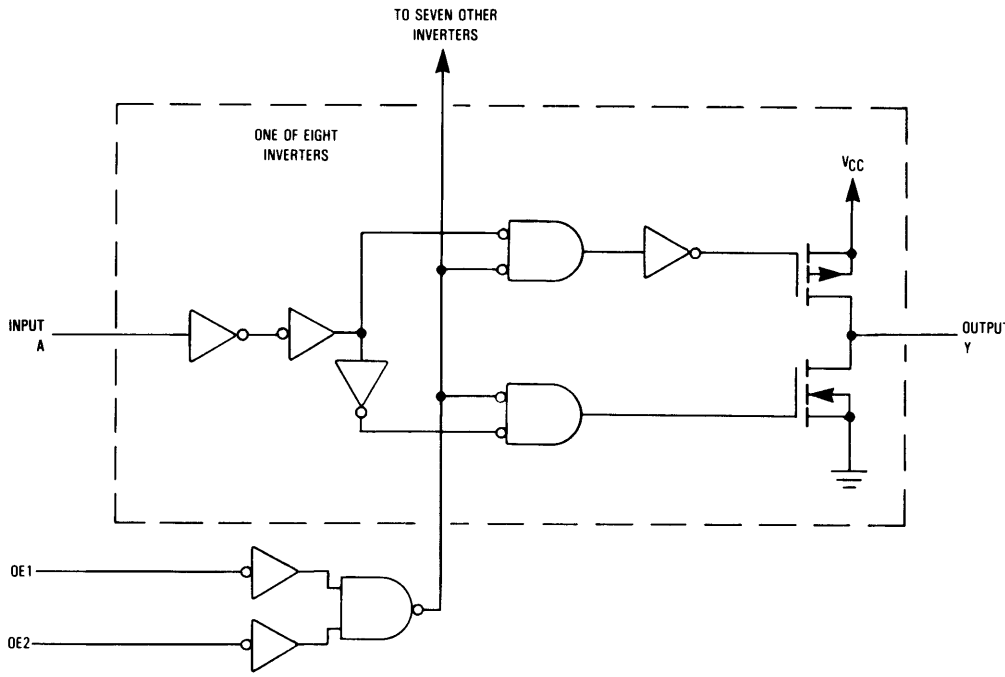
CONTROLS

OE1, OE2 (PINS 1, 19) — Output enables (active low). When a low level is applied to both of these pins, the outputs are enabled and the device functions as an inverter. When a high level is applied to either input, the outputs assume the high impedance state.

OUTPUTS

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11) — Device outputs. Depending upon the state of the output-enable pins, these outputs are either inverting outputs or high impedance outputs.

LOGIC DETAIL



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